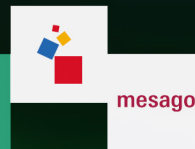


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for Power Electronics, Intelligent Motion,  
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## → Contents

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# PCIM Asia 2023 Conference Welcome Address



Dear PCIM Asia participants,

I am very happy and proud to welcome all of you to the PCIM Asia Conference and Exhibition 2023 in Shanghai.

The PCIM Asia Conference brings together the world's foremost experts and decision maker from industry and academia in the field of power electronic components and systems to discuss future technology trends and launching new products in the market. Power electronic components and energy conversion systems today are driven by WBG technologies, the electrification of all transportation vehicles, renewable energy technologies, communication equipment and artificial intelligence. WBG devices gives a new freedom in the design of ultra-high power density converters along with high efficiency ratings. Researchers from academia and experts from industry will provide presentations covering new developments in the field of power devices, advanced packaging technologies with outstanding reliability, future power converters for automotive and renewable energy systems. This year in our technical program we are covering innovations along the power electronic roadmap in addition to three leading experts for keynote presentations, one special session on GaN based high power density supplies and one tutorial on advanced power modules. The PCIM Asia is a worldwide magnet for design engineers and researchers in the field of power electronics as well as decision makers from companies to generate new market segments and trigger future research directions.

## **Important innovations on components and system level will be outlined during this year's PCIM Asia Conference**

The technical program of this year's PCIM Asia is covering new development achievements on power semiconductor devices based on Si and WBG technologies including relevant packaging designs handling ultrafast switching devices with extended lifetime and sensing parameters for predictive diagnostic functions as well as smart digital controlled power conversion concepts for traction and grid applications.

## **Conference highlights and future milestones in the value-added chain of power electronics**

The keynote presentations on the new generation of GaN power devices, packaging designs for high power density and high voltage capabilities as well as dedicated high voltage semiconductor switches for wind power applications together with GaN based ultra-high power density power supplies will attract many power electronics experts.

Special attention has been paid to research carried out by engineers from industries and universities with their presentations and "Best Paper Award", "Young Engineer Award" and "University Scientist Award" during the PCIM Asia conference 2023 – these are certainly further highlights of the conference.

I wish you an enjoyable and successful conference, an open dialog with all the experts and packed with new ideas for your future product innovation and business.

*Leo Loser*

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## Table of Content PCIM Asia Conference 2023

### Keynote

- 1 The new generation of Gallium Nitride Power devices; breaking the limits of ease-of-use and reliability ..... 16**  
Florin Udrea, Cambridge GaN Devices Ltd., UK

### IGBT and SiC Devices

- 2 A Snapback-Free Reverse-Conducting IGBT with P floating region at Collector ..... 23**  
Wuhua Yang, Cailin Wang, Wanting Du, Chao Zhang, Xi'an University of Technology, China



pcim Asia  
Young Engineer Award  
**FINALIST**

- 3 Accurate Switching Behavior Modeling for SiC MOSFETs Considering Dynamic Output Characteristics ..... 27**  
Yimin Zhou, Zhiqiang Wang, Yayong Yang, Guoqing Xin, Xiaojie Shi, Yong Kang, Huazhong University of Science and Technology, China



pcim Asia  
Best Paper Award  
**WINNER**

- 4 More than an Evolution: a New Power MOSFET Technology for Higher Efficiency of Power Supplies ..... 33**  
Owen Song, Infineon Semiconductors Company Ltd., China  
Ralf Seimieniec, Simone Mazzer, Cesar Braz, Gerhard Noebauer, Michael Hutzler, David Laforet, Elias Pree, Alessandro Ferrara, Infineon Technologies Austria AG, Austria
- 5 Modeling and Validation of a Silicon-Carbide Power Module ..... 40**  
Lizhen Zhang, Roveendra Paul, James Victory, Bo Tian, onsemi, USA  
Dylan Cho, onsemi, South Korea

## Advanced Control and Associated Hardware



pcim Asia  
Best Paper Award  
**FINALIST**

- 6 Impedance Based Beat Suppression Strategy for PMSM Drives with Small DC-Link Capacitors ..... 48**  
Dawei Ding, Runfeng Gao, Zekun Ren, Weixin Yue, Gaolin Wang, Dianguo Xu, Harbin Institute of Technology, China
- 7 Reducing steady state losses in High performance Charger Topologies with easy to use GaN HEMTs ..... 52**  
Martin Cheung, Cambridge GaN Devices, UK  
(Abstract)
- 8 Discussion on Power Module Solutions for 200kW Power Converter System in Energy Storage System ..... 54**  
Jie Dong, Xin Hao, Industry Power Control Infineon Science and Technology (China) Company Limited, China



pcim Asia  
University Scientist Award  
**FINALIST**

- 9 Analysis of Input Current Distortion in Three-phase Current Source PWM Rectifier ..... 60**  
Binghui Li, Shuhan Zhou, Mingzhi He, Yanzi Zhang, School of Electrical Engineering, Sichuan University, China  
Gao Liu, Department of Energy Technology, Aalborg University, Denmark

## Power Semiconductor Devices



pcim Asia  
University Scientist Award  
**FINALIST**

- 10 A Trench Gate Reverse-Conducting IGBT with a Shallow Oxide Trench and a Floating P-Region ..... 65**  
Wuhua Yang, Cailin Wang, Ronghua Cheng, Ruliang Zhang, Xi'an University of Technology, China
- 11 The Research on Influencing Factors of 650V IGBT's Turn-off  $dV_{ce}/dt$  Controllability ... 70**  
Rui Li, Keqiang Ma, Siliang Wang, Yi Xiang, Liangkai Liu, Ke Yang, Chengdu Semi-Future Technology Co., Ltd., China

- 12 Research on discrete IGBT7 H7 1200 V in inverter for Solar and UPS applications ..... 74**  
Ming Zhou, Infineon Semiconductor (Shenzhen) Co. Ltd., China  
Liwei Zhou, Infineon Technologies China Co. Ltd., China



pcim Asia  
University Scientist Award

- 13 FINALIST Driver Optimization Method Based on GeneticAlgorithm for IGBT ..... 78**  
Chengyang Lin, Mingcheng Ma, Tianlin Sun, Dianguo Xu, Harbin Institute of Technology, China



pcim Asia  
University Scientist Award

- 14 FINALIST A Variable Bypass Current Source Driver Circuit Based on Reference Voltage ..... 84**  
Mingcheng Ma, Chengyang Lin, Tianlin Sun, Dianguo Xu, Harbin Institute of Technology, China

- 15 Research on the Full Temperature Range Characteristics of IGBT ..... 90**  
Tianlin Sun, Chengyang Lin, Mingcheng Ma, Dianguo Xu, Harbin Institute of Technology, China

- 16 Gate oxide degradation of SiC IGBT induced by non-constant thermal-electrical coupled-stresses ..... 97**  
Rongde Luo, Fugen Wu, State Key Laboratory of Precision Electronic Manufacturing Technology and Equipment, Guangdong University of Technology, China  
Rongde Luo, Fugen Wu, School of Materials and Energy, Guangdong University of Technology, China  
Shaodong Yang, Xia Luo, Hao Niu, Xianjun Kuang, Zongbei Dai, No.5 Electronics Research Institute of the Ministry of Industry and Information Technology, China  
Xiaowei Xu, Three Gorges Intelligent Industrial Control Technology Company, China  
Huafeng Dong, School of Physics and Optoelectronic Engineering, Guangdong University of Technology, China

## Motion Control



pcim Asia  
University Scientist Award

WINNER

- 17** **Direct Pressure-tolerant DC Transformer Scheme and Control Method Applied to Subsea Power Supply** ..... 103  
Zedong Zheng, Jiye Liu, Department of Electrical Engineering, Tsinghua University, China  
Lisha Chen, Chi Li, Energy Internet Innovation Institute of Tsinghua University, China
- 18** **A New Parameter-free Predictive Current Control for PMSM** .....111  
Guofu Zhang, Xiaoguang Zhang, North China University of Technology, China
- 19** **Multi-stage model predictive current control with parameters-free for PMSM drives** .. 117  
Zhen Wu, Xiaoguang Zhang, North China University of Technology, China
- 20** **An improved four-vector model for predictive current control used for PMSM drives** 122  
Shujun Fang, Xiaoguang Zhang, Ji Li, North China University of Technology, China
- 21** **Derivation of DC Servo Driver Current Loop Model** ..... 128  
Bin Han, Jing Qiu, Lian Yungang JARI Electronics Co., Ltd., China  
Ming Yang, Harbin Institute of Technology, China
- 22** **Self-tuning Technique of PMSM Current Loop Based on Active Damping** ..... 134  
Qiu Jing, Yuchen Song, Lian Yungang JARI Electronics Co., Ltd., China  
Ming Yang, Harbin Institute of Technology, China

## Power Converters

- 23** **Development of algorithm to control switched-mode power supply for charging battery based on extended Kalman filter** ..... 140  
Nikolai Kalugin, Aleksei Chernyshov, EnerGet, LLC, Russia
- 24** **Universal mathematical model of single-phase DC-DC bridge converter for different control algorithms** ..... 147  
Yury Skorokhod, Dmitriy Sorokin, Transconverter Ltd., Russian Federation  
Sergey Volskiy, Moscow Aviation Institute (Technical University), Russian Federation
- 25** **Development of the control algorithm for the two-unit fast-charging stations** ..... 153  
Nikolay Volskiy, Mikhail Krapivnoi, Charge Evolution Ltd., Russian Federation  
Darja Barkovska, Internic Ltd., Latvia




- 26 Panoramic co-simulation technology for large-scale offshore wind power..... 159**  
Junyang Zhang, Xiaojiang Guo, Zheng Li, China Huaneng Clean Energy Research Institute, China
- 27 A Cooperative Control Strategy for AC Fault Ride Through of Offshore Wind Power Based on AC Voltage Fluctuation ..... 164**  
Chunhua Li, Yijing Chen, Xiaojiang Guo, Xuhui Shen, Sun Xu, China Huaneng Group Clean Energy Research Institute, China

## Si and WBG Devices Part I

- 28 2.3kV Si and SiC devices development for renewable energy system ..... 169**  
Shuangching Chen, Yusuke Sekino, Taku Takaku, Keiji Okumura, Takafumi Uchida, Kaname Mitsuzuka, Yuichi Onozawa, Yoshiyuki Kusunoki, Yasuyuki Kobayashi, Fuji Electric Co. Ltd., Japan  
Chen Song, Fuji Electric Co. Ltd., China
- 29 Wide Bandgap Semiconductor – a foundry perspective ..... 174**  
Heming Wei, X-FAB Sarawak Sdn. Bhd., Malaysia  
Agnes Jahnke, X-FAB Global Services GmbH, Germany
- 30 Using Test-to-Fail Methodology to Predict How GaN Devices Can Last More than 25 Years in Solar Applications ..... 179**  
Shengke Zhang, Siddhesh Gajare, Ricardo Garcia, Efficient Power Conversion Corporation, USA



pcim Asia  
University Scientist Award

- 31  Implantation optimization for 1200 V SiC MPS with ultra-low leakage current and high surge current capability ..... 187**  
Bo Yi, Yi Xu, Junji Cheng, Hongqiang Yang, University of Electronic Science and Technology of China, China  
Keqiang Ma, Siliang Wang, Xingli Jiang, Qiang Hu, Chengdu Semi-Future Technology Co., Ltd., China

## Converters

- 32 The Power loss reduction from continuous PWM to discontinuous PWM in a 3L ANPC converter ..... 190**  
Heng Wang, Infineon Integrated Circuit (Beijing) Co., Ltd., China  
Yixuan Wang, Infineon China Technologies, China

- 33 A SiC Based 3.6kW High Efficiency and High Power Density PFC Converter for Off-line Switching Mode Power Supplies..... 195**

Ying Liu, Kevin Xie, Wolfspeed, China  
Yuequan Hu, Anuj Narain, Wolfspeed, USA



pcim Asia  
University Scientist Award

- 34 WINNER A Control Strategy Enabling Compatible 1-Ph/3-Ph V2L Operations for EV Chargers with Improved Leg Utilizations ..... 199**

Peng Chen, Ziheng Yuan, Zhouyu Wu, Wei Wu, Helong Li, Zhiqing Yang, Shuang Zhao, Zixiang Yu, Lijian Ding, Hefei University of Technology, China  
Lijun Wang, Wei Huo, OAKFORESEE INTELLIMOBILE TECH Co., Ltd., China

- 35 3MHz GaN DC-DC 48Vin direct to 0.6Vout realized by ultra-short pulse (5ns) using Virtual Peak Current Mode control technique ..... 205**

Isao Takobe, Hiroshi Yamashita, Junki Otani, Akihiro Kawano, Toshiyuki Zaitso, ROHM Co., Ltd., Japan

## Keynote

- 36 Packaging and Integration of Wide-Bandgap Power Semiconductors: Challenges and Opportunities..... 211**

Christina DiMarino, Virginia Polytechnic Institute and State University, USA  
(Abstract)

## Si and WBG Devices Part II

- 37 A Full SiC 60kW Three Phase LLC Converter for Fast Charger..... 212**

Chen Wei, Zongzeng Hu, Jianlong Chen, Fulin Zhang, Wolfspeed, China  
Anuj Narain, Wolfspeed, USA

- 38 Tuning GaN switching performance and operation in parallel within a bridge topology ..... 218**

Peter Comiskey, Cambridge GaN Devices, UK  
(Abstract)

- 39 1.2 KV SOI level-shift gate driver with Miller clamp and short circuit clamp to drive SiC MOSFETs..... 222**

Weidong Chu, Infineon Technologies Americas Corp., USA

- 40 A four-chip parallel IGBT module based on the latest generation technology used in Photovoltaic Centralized Inverter ..... 227**  
 Tao Zhang, Wang Xuanxuan, Rong Rui, Cao Shuai, Miao Shuo, Chen Guokang, Macmic Science & Technology Co., Ltd., China

**Automotive Applications**

- 41 Low loss and High-cooling-performance automotive power module for 160 kW EV application ..... 232**  
 Yoshihisa Ebuchi, Naoya Shimada, Yoshihiko Kawakami, Youichiro Seki, Manabu Watanabe, Souichi Yoshida, Yuuta Takeuchi, Yoshihiro Tateishi, Fuji Electric Co., Ltd., Japan
- 42 An advanced SiC power module designated for automotive ..... 236**  
 Hideo Komo, Rei Yoneyama, Shoichi Orita, Gourab Majumdar, Mitsubishi Electric Corporation, Japan
- 43 Fast-Charging Commercial Vehicles – A Megawatt Application Similar to Electrolysis ..... 243**  
 Martin Schulz, Littelfuse Europe GmbH, Germany
- 44 New Generation 750V IGBT modules for automotive application ..... 248**  
 Zhihong Liu, Yi Tang, Jinchun Yan, Fu Yong, Songlin Zheng, Jiajie Ma, Ye Chen, Xi Ling, Lijun Yao, StarPower Semiconductor Ltd., China

**Power Semiconductor Modules**

- 45 60kW Dual Active Bridge Converter based on 4-in-1 SiC MOSFET Module for PET Application ..... 254**  
 Jian Sun, Bo Hu, Gaosheng Song, Mitsubishi Electric & Electronics (Shanghai) Co., Ltd., China
- 46 Thermal model of fully-molded, multi-chip power modules ..... 258**  
 Sungmo Young, Taejin Lee, Hyukdong Kwon, Infineon Technologies Korea, South Korea
- 47 Introduction of RC-IGBT Based Transfer Mold SOIPM™ ..... 263**  
 Xiaoling Wang, Mitsubishi Electric & Electronics (Shanghai) Co., Ltd., China  
 Jian Chen, Mitsubishi Electric GEM Power Device (Hefei) Co., Ltd., China  
 Akiko Goto, Power Device Works, Mitsubishi Electric Corporation, Japan

**48 30A/600V RC-IGBT Based Transfer Molded IPM for Home Appliance Application..... 267**  
 Kai Jiang, Mitsubishi Electric & Electronics (Shanghai) Co., Ltd., China  
 Motonobu Joko, Power Device Works, Mitsubishi Electric Corporation, Japan  
 Hongguang Huang, Mitsubishi Electric & Electronics (Shanghai) Co., Ltd., China

**49 An 820A 750V IGBT Module with Excellent Performance for Inverter of Electric Vehicle.....271**  
 Shuo Miao, Rui Rong, Chao Chen, Tao Zhang, Shuai Cao, Guokang Chen, Yadong Meng, Macmic Science & Technology Co., Ltd., China

**50 3rd Generation RC-IGBT for Automotive Application .....274**  
 Kentaro Yoshida, Shintaro Araki, Tsuyoshi Osaga, Seiichiro Inokuchi, Power Device Works, Mitsubishi Electric Corp., Japan

**51 3-level T-type 4-in-1 Module for Active Front End Solution ..... 277**  
 Haruki Murakami, Nobuya Nishida, Mitsubishi Electric Corporation, Japan  
 Siqing Lu, Yuancheng Zhang, Mitsubishi Electric & Electronics (Shanghai) Co., Ltd., China

**Packaging Technologies**

**52 Study on Microstructure and Mechanical Properties of Copper-Copper Bonding by Ultrasonic Welding ..... 280**  
 Xiankun Zhang, Xiaofei Pang, Xiaodong Zhang, Jianning Zhang, China Resources Runan Chongqing Co., Ltd., China

**53 Study on harmonic response of wirebond in high power IGBT module under ultrasonic welding process..... 284**  
 Xingfeng Li, Jianxin Huang, Zhangzhen Luo, Guiqin Chang, Tinchang Shi, Haihui Luo, Qiang Xiao, Zhuzhou CRRC Times Semiconductor Co., Ltd., China  
 Xingfeng Li, Jianxin Huang, Zhangzhen Luo, Guiqin Chang, Tinchang Shi, Haihui Luo, Qiang Xiao, State Key Laboratory of Power Semiconductor and Integration Technology, China



**pcim Asia**  
 University Scientist Award

**54 WINNER Optimization of Pinfin Heat Sink for SiC Power Module based on LBM-LES .....291**  
 Jian Cui, Puqi Ning, Xiaoshuang Hui, University of Chinese Academy of Sciences, China  
 Jian Cui, Puqi Ning, Xiaoshuang Hu, Institute of Electrical Engineering, Chinese Academy of Sciences, China  
 Jian Cui, State grid Shaoxing Electric Power Company, Ltd., China



**pcim Asia**  
Young Engineer Award  
**WINNER**

- 55 An Accurate 3D Thermal Simulation Method Based on Neural Network-Aided Power Loss Model ..... 299**  
Yayong Yang, Zhiqiang Wang, Yimin Zhou, Guoqing Xin, Xiaojie Shi, Yong Kang, Huazhong University of Science and Technology, China
- 56 Research on the improvement of IGBT module surge capability..... 305**  
Chao Fang, Guiqin Chang, Xi Zou, Haihui Luo, Qiang Xiao, Yangang Wang, Zhuzhou CRRC Times Semiconductor Ltd., China  
Chao Fang, Guiqin Chang, Xi Zou, Haihui Luo, Qiang Xiao, Yangang Wang, State Key Laboratory of Power Semiconductor and Integration Technology, China
- 57 A 1200V 600A Full SiC Half-Bridge Power Module with Low Inductance and Good Current Balancing Performance ..... 309**  
Wenbo Wang, Jingru Dai, Yangang Wang, Dynex Semiconductor Ltd., UK
- 58 Low-Loss Molding Inductors analysis ..... 314**  
Kunming Tsuo, Bourns Inc., Taiwan, China  
David Wiest, Bourns Inc., USA

**Packaging and Reliability**

- 59 Application benefits of TO-247 PLUS package reflow soldering in vehicle traction inverter ..... 319**  
Zhenbo Zhao, Hao Zhang, Infineon Technologies Center of Competence (Shanghai) Co., Ltd., China
- 60 Method of avoiding plastic IGBT module’s torque loss in harsh application environment..... 323**  
Cao Shuai, Chao Chen, Rui Rong, Tao Zhang, Shuo Miao, Macmic Science & Technology Co., Ltd., China



**pcim Asia**  
Best Paper Award  
**FINALIST**

- 61 Comprehensive Loss and Thermal Performance Analysis of Three-level T-type Grid-connected Converter ..... 328**  
Liangliang Han, Wei Wu, Man Zhang, Helong Li, Zhiqing Yang, Shuang Zhao, Lijian Ding, Hefei University of Technology, China  
Shuai Deng, Zhenyang Li, Anhui Hanxing Energy Co., Ltd., China



pcim Asia  
Best Paper Award

- 62 FINALIST Gate Circuit improves p-GaN HEMT  $V_{TH}$  reliability ..... 334**  
 Xinke Liu, Zengfa Chen, Ze Zhong, Qiyan Zhang, Xiaobo Li, Shuangwu Huang, Linfei Gao, College of Materials Science and Engineering, College of Electronics and Information Engineering, Institute of Microelectronics, Guangdong Research Center for Interfacial Engineering, State Key Laboratory of Radio Frequency Heterogeneous Integration, Shenzhen University, China  
 Feng Qiu, Yong Xu, Gensol (Shenzhen) Tech. Innovation Center Co., Ltd., China  
 Wenrong Zhuang, Dongguan Sino Nitride Semiconductor Co., Ltd., China  
 Longkou Chen, Shenzhen Baseus Technology Co., Ltd., China

## High Power and Grid Applications

- 63 Distributed Real-Time Simulation System for Power Converter-Dominated Grid..... 342**  
 Peilin Zhang, Zhiyu Cao, Avasition Electric Co. Ltd., Hangzhou, China  
 Yilong Cao, Haoyang Cui, Shanghai University of Electric Power, China



pcim Asia  
University Scientist Award

- 64 WINNER The MMC Based DC Transformer with Reshaped Circulating Current ... 348**  
 Wenlong Hou, Xiaodong Zhao, Binbin Li, Dianguo Xu, School of Electrical Engineering, Harbin Institute of Technology, China
- 65 New generation high power semiconductors for 8GW VSC-HVDC applications ..... 354**  
 Evgeny Tsyplakov, Gaurav Gupta, Jeremy Jones, B. Boksteen, L. D. Michelis, Christian Winter, Makan Chen, Hitachi Energy Switzerland Ltd. Semiconductors, Switzerland  
 Jan Vobecky, Hitachi Energy s.r.o. Semiconductors, Czech Republic



pcim Asia  
Young Engineer Award

- 66 FINALIST Active Power Decoupling Based on Input Current Ripple Control for Single-Phase Voltage Source Inverter..... 360**  
 Xun Jiang, Meiqin Mao, Wei Cheng, Research Center for Photovoltaic System Engineering of Ministry of Education, Hefei University of Technology, China  
 Liuchen Chang, University of New Brunswick, Canada

## Keynote

- 67 Power Semiconductor Devices on Windpower Applications ..... 368**  
Dapeng Zheng, Shenzhen Hopewind Electric, CN  
(Contact Page)

## Special Session: GaN based High Power Density Supplies

- 68 GaN switches enable high performance architecture for USB-PD EPR Adaptors ..... 369**  
Pierrick Ausseresse, Alfredo Medina-Garcia, Josef Daimer, Infineon Technologies AG, Germany  
Manfred Schlenk, Dr. Schlenk Consulting, Germany
- 69 EMI suppression techniques for very high efficiency and very high-power density medium power AC-DC adapters ..... 377**  
Ionel Jitaru, Rompower Energy Systems Inc., USA  
Andrei Savu, Rompower International SRL, Romania  
Constantin Radoi, Polyethnic University of Bucharest, Romania
- 70 Value Proposition of Integrated GaN Solutions for Low to Medium Range Power Applications ..... 382**  
Dong Li, Infineon Technologies Asia Pacific Pte. Ltd., Singapore  
(Abstract)

## Tutorial

- 71 High-Performance Power Modules and SiC Devices ..... 383**  
Haihui Luo, Zhuzhou CRRC Times Semiconductor Co., Ltd., China  
(Contact Page)

## Authors Index PCIM Asia Conference 2023

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Cao	Zhiyu	Avasition Electric Co. Ltd.	China
Chang	Guiqin	Zhuzhou CRRC Times Semiconductor Co. Ltd. State Key Laboratory of Power Semiconductor and Integration Technology	China
Chang	Liuchen	University of New Brunswick	Canada
Chen	Chao	Macmic Science & Technology Co. Ltd.	China
Chen	Guokang	Macmic Science & Technology Co. Ltd.	China
Chen	Jian	Mitsubishi Electric GEM Power Device (Hefei) Co. Ltd.	China
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Chen	Peng	Hefei University of Technology	China
Chen	Shuangching	Fuji Electric Co. Ltd.	Japan
Chen	Ye	Starpower Semiconductors Ltd.	China
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Chu	Weidong	Infineon Technologies Americas Corp.	USA



Last Name	First Name	Organisation	Country
Constantin	Radoi	Polyethnic University of Bucharest	Romania
Cui	Haoyang	Shanghai University of Electric Power	China
Cui	Jian	University of Chinese Academy of Sciences Institute of Electrical Engineering, Chinese Academy of Sciences State Grid Shaoxing Electric Power Company	China
<b>D</b>			
Dai	Jingru	Dynex Semiconductor Ltd.	UK
Dai	Zongbei	No.5 Electronics Research Institute of the Ministry of Industry and Information Technology	China
Daimer	Josef	Infineon Technologies AG	Germany
Deng	Shuai	Anhui Hanxing Energy Co. Ltd.	China
DiMarino	Christina	Virginia Tech	USA
Ding	Dawei	Harbin Institute of Technology	China
Ding	Lijian	Hefei University of Technology	China
Dong	Huafeng	Guangdong University of Technology	China
Dong	Jie	Industry Power Control Infineon Science and Technology (China) Company Limited	China
Du	Wanting	Xi'an University of Technology	China
<b>E</b>			
Ebuchi	Yoshihisa	Fuji Electric Co. Ltd.	Japan
<b>F</b>			
Fang	Chao	Zhuzhou CRRC Times Semiconductor Co. Ltd. State Key Laboratory of Power Semiconductor and Integration Technology	China
Fang	Shujun	North China University of Technology	China
Ferrara	Alessandro	Infineon Technologies Austria AG	Austria
<b>G</b>			
Gajare	Siddhesh	Efficient Power Conversion Corporation	USA
Gao	Linfei	College of Materials Science and Engineering, College of Electronics and Information Engineering, Institute of Microelectronics, Guangdong Research Center for Interfacial Engineering, State Key Laboratory of Radio Frequency Heterogeneous Integration, Shenzhen University	China
Gao	Runfeng	Harbin Institute of Technology	China
Garcia	Ricardo	Efficient Power Conversion Corporation	USA
Goto	Akiko	Mitsubishi Electric Corporation	Japan
Guo	Xiaojiang	China Huaneng Clean Energy Research Institute	China
Gupta	Gaurav	Hitachi Energy Switzerland Ltd. Semiconductors	Switzerland
<b>H</b>			
Han	Bin	Lian Yungang JARI Electronics Co. Ltd.	China

Last Name	First Name	Organisation	Country
Han	Liangliang	Hefei University of Technology	China
Hao	Xin	Industry Power Control Infineon Science and Technology (China) Company Limited	China
He	Mingzhi	Sichuan University	China
Hou	Wenlong	Harbin Institute of Technology	China
Hu	Bo	Mitsubishi Electric & Electronics (Shanghai) Co. Ltd.	China
Hu	Qiang	Chengdu Semi-Future Technology Co. Ltd.	China
Hu	Yuequan	Wolfspeed	USA
Hu	Zongzeng	Wolfspeed	China
Huang	Hong Guang	Mitsubishi Electric & Electronics (Shanghai) Co. Ltd.	China
Huang	Jianxin	Zhuzhou CRRC Times Semiconductor Co. Ltd.	China
Huang	Shuangwu	College of Materials Science and Engineering, College of Electronics and Information Engineering, Institute of Microelectronics, Guangdong Research Center for Interfacial Engineering, State Key Laboratory of Radio Frequency Heterogeneous Integration, Shenzhen University	China
Hui	Xiaoshuang	University of Chinese Academy of Sciences Institute of Electrical Engineering, Chinese Academy of Sciences	China
Huo	Wei	OAKFORESEE INTELLIMOBILE TECH Co. Ltd.	China
Hutzler	Michael	Infineon Technologies Austria AG	Austria
<b>I</b>			
Inokuchi	Seiichiro	Mitsubishi Electric Corp.	Japan
<b>J</b>			
Jahnke	Agnes	X-FAB Global Services GmbH	Germany
Jiang	Kai	Mitsubishi Electric & Electronics (Shanghai) Co. Ltd.	China
Jiang	Xingli	Chengdu Semi-Future Technology Co. Ltd.	China
Jiang	Xun	Hefei University of Technology	China
Jitaru	Ionel	Rompower Energy Systems Inc.	USA
Joko	Motonobu	Mitsubishi Electric Corporation	Japan
Jones	Jeremy	Hitachi Energy Switzerland Ltd. Semiconductors	Switzerland
<b>K</b>			
Kalugin	Nikolai	EnerGet, LLC	Russia
Kang	Yong	Huazhong University of Science and Technology	China
Kawakami	Yoshihiko	Fuji Electric Co. Ltd.	Japan
Kawano	Akihiro	ROHM Co. Ltd.	Japan
Kobayashi	Yasuyuki	Fuji Electric Co. Ltd.	Japan
Komo	Hideo	Mitsubishi Electric Corporation	Japan
Krapivnoi	Mikhail	Charge Evolution Ltd	Russian Federation

Last Name	First Name	Organisation	Country
Kuang	Xianjun	No.5 Electronics Research Institute of the Ministry of Industry and Information Technology	China
Kusunoki	Yoshiyuki	Fuji Electric Co. Ltd.	Japan
Kwon	Hyukdong	Infineon Technologies Korea	South Korea
<b>L</b>			
Laforet	David	Infineon Technologies Austria AG	Austria
Lee	Taejin	Infineon Technologies Korea	South Korea
Li	Binbin	Harbin Institute of Technology	China
Li	Binghui	Sichuan University	China
Li	Chi	Energy Internet Innovation Institute of Tsinghua University	China
Li	Chunhua	China Huaneng Group Clean Energy Research Institute	China
Li	Dong	Infineon Technologies Asia Pacific Pte. Ltd.	Singapore
Li	Helong	Hefei University of Technology	China
Li	Ji	North China University of Technology	China
Li	Rui	Chengdu Semi-Future Technology Co. Ltd.	China
Li	Xiaobo	College of Materials Science and Engineering, College of Electronics and Information Engineering, Institute of Microelectronics, Guangdong Research Center for Interfacial Engineering, State Key Laboratory of Radio Frequency Heterogeneous Integration, Shenzhen University	China
Li	Xingfeng	Zhuzhou CRRR Times Semiconductor Co. Ltd.	China
Li	Zheng	China Huaneng Clean Energy Research Institute	China
Li	Zhenyang	Anhui Hanxing Energy Co. Ltd.	China
Lin	Chengyang	Harbin Institute of Technology	China
Ling	Xi	Starpower Semiconductors Ltd	China
Liu	Gao	Aalborg University	Denmark
Liu	Jiye	Tsinghua University	China
Liu	Liangkai	Chengdu Semi-Future Technology Co. Ltd.	China
Liu	Xinke	College of Materials Science and Engineering, College of Electronics and Information Engineering, Institute of Microelectronics, Guangdong Research Center for Interfacial Engineering, State Key Laboratory of Radio Frequency Heterogeneous Integration, Shenzhen University	China
Liu	Ying	Wolfspeed	China
Liu	Zhihong	Starpower Semiconductors Ltd.	China
Lu	Siqing	Mitsubishi Electric & Electronics (Shanghai) Co. Ltd.	China
Luo	Haihui	Zhuzhou CRRR Times Semiconductor Co. Ltd., State Key Laboratory of Power Semiconductor and Integration Technology	China
Luo	Rongde	Guangdong University of Technology	China
Luo	Xia	No.5 Electronics Research Institute of the Ministry of Industry and Information Technology	China
Luo	Zhangzhen	Zhuzhou CRRR Times Semiconductor Co. Ltd.	China

Last Name	First Name	Organisation	Country
<b>M</b>			
Ma	Jiajie	Starpower Semiconductors Ltd.	China
Ma	Keqiang	Chengdu Semi-Future Technology Co. Ltd.	China
Ma	Mingcheng	Harbin Institute of Technology	China
Majumdar	Gourab	Mitsubishi Electric Corporation	Japan
Mao	Meiqin	Hefei University of Technology	China
Mazzer	Simone	Infineon Technologies Austria AG	Austria
Medina-Garcia	Alfredo	Infineon Technologies AG	Germany
Meng	Yadong	Macmic Science & Technology Co. Ltd.	China
Miao	Shuo	Macmic Science & Technology Co. Ltd.	China
Michelis	L. D.	Hitachi Energy Switzerland Ltd. Semiconductors	Switzerland
Mitsuzuka	Kaname	Fuji Electric Co. Ltd.	Japan
Murakami	Haruki	Mitsubishi Electric Corporation	Japan
<b>N</b>			
Narain	Anuj	Wolfspeed	USA
Ning	Puqi	University of Chinese Academy of Sciences Institute of Electrical Engineering, Chinese Academy of Sciences	China
Nishida	Nobuya	Mitsubishi Electric Corporation	Japan
Niu	Hao	No.5 Electronics Research Institute of the Ministry of Industry and Information Technology	China
Noebauer	Gerhard	Infineon Technologies Austria AG	Austria
<b>O</b>			
Okumura	Keiji	Fuji Electric Co. Ltd.	Japan
Onozawa	Yuichi	Fuji Electric Co. Ltd.	Japan
Orita	Shoichi	Mitsubishi Electric Corporation	Japan
Osaga	Tsuyoshi	Mitsubishi Electric Corp.	Japan
Otani	Junki	ROHM Co. Ltd.	Japan
<b>P</b>			
Pang	Xiaofei	China Resources Runan Chongqing Co. Ltd.	China
Paul	Roveendra	onsemi	USA
Peter	Comiskey	Cambridge GaN Devices	UK
Pree	Elias	Infineon Technologies Austria AG	Austria
<b>Q</b>			
Qiu	Feng	Gensol (Shenzhen) Tech. Innovation Center Co. Ltd.	China
Qiu	Jing	Lian Yungang JARI Electronics Co., Ltd.	China

Last Name	First Name	Organisation	Country
<b>R</b>			
Ren	Zekun	Harbin Institute of Technology	China
Rong	Rui	Macmic Science & Technology Co. Ltd.	China
<b>S</b>			
Schlenk	Manfred	Dr. Schlenk Consulting	Germany
Schulz	Martin	Littelfuse Europe GmbH	Germany
Seki	Youichirou	Fuji Electric Co. Ltd.	Japan
Sekino	Yusuke	Fuji Electric Co. Ltd.	Japan
Shen	Xuhui	China Huaneng Group Clean Energy Research Institute	China
Shi	Tinchang	Zhuzhou CRRC Times Semiconductor Co. Ltd.	China
Shi	Xiaojie	Huazhong University of Science and Technology	China
Shimada	Naoya	Fuji Electric Co. Ltd.	Japan
Siemieniec	Ralf	Infineon Technologies Austria AG	Austria
Skorokhod	Yury	Transconverter Ltd.	Russian Federation
Song	Chen	Fuji Electric Co. Ltd.	China
Song	Gaosheng	Mitsubishi Electric & Electronics (Shanghai) Co. Ltd.	China
Song	Owen	Infineon Semiconductors Company Ltd.	China
Song	Yuchen	Lian Yungang JARI Electronics Co. Ltd.	China
Sorokin	Dmitriy	Transconverter Ltd.	Russian Federation
Sun	Jian	Mitsubishi Electric & Electronics (Shanghai) Co. Ltd.	China
Sun	Tianlin	Harbin Institute of Technology	China
<b>T</b>			
Takaku	Taku	Fuji Electric Co. Ltd.	Japan
Takeuchi	Yuuta	Fuji Electric Co. Ltd.	Japan
Takobe	Isao	ROHM Co. Ltd.	Japan
Tang	Yi	Starpower Semiconductors Ltd	China
Tateishi	Yoshihiro	Fuji Electric Co. Ltd.	Japan
Tian	Bo	onsemi	USA
Tsuo	Kunming	Bourns, Inc Taiwan	Taiwan, China
Tsyplakov	Evgeny	Hitachi Energy Switzerland Ltd. Semiconductors	Switzerland
<b>U</b>			
Uchida	Takafumi	Fuji Electric Co. Ltd.	Japan
Udrea	Florin	Cambridge GaN Devices Ltd.	UK

Last Name	First Name	Organisation	Country
<b>V</b>			
Victory	James	onsemi	USA
Vobecky	Jan	Hitachi Energy s.r.o. Semiconductors	Czech Republic
Volskiy	Nikolay	Charge Evolution Ltd.	Russian Federation
Volskiy	Sergey	Moscow Aviation Institute (Technical University)	Russian Federation
<b>W</b>			
Wang	Gaolin	Harbin Institute of Technology	China
Wang	Heng	Infineon Integrated Circuit (Beijing) Co. Ltd.	China
Wang	Lijun	OAKFORESEE INTELLIMOBILE TECH Co. Ltd.	China
Wang	Siliang	Chengdu Semi-Future Technology Co. Ltd.	China
Wang	Wenbo	Dynex Semiconductor Ltd.	UK
Wang	Xiaoling	Mitsubishi Electric & Electronics (Shanghai) Co. Ltd.	China
Wang	Xuanxuan	Macmic science & technology Co. Ltd.	China
Wang	Yangang	Dynex Semiconductor Ltd.	UK
Wang	Yangang	Zhuzhou CRRRC Times Semiconductor Co. Ltd. State Key Laboratory of Power Semiconductor and Integration Technology	China
Wang	Yixuan	Infineon China Technologies	China
Wang	Zhiqiang	Huazhong University of Science and Technology	China
Watanabe	Manabu	Fuji Electric Co. Ltd.	Japan
Wei	Chen	Wolfspeed	China
Wei	Heming	X-FAB Sarawak Sdn. Bhd	Malaysia
Wiest	David	Bourns, Inc USA	USA
Winter	Christian	Hitachi Energy Switzerland Ltd. Semiconductors	Switzerland
Wu	Fugen	Guangdong University of Technology	China
Wu	Wei	Hefei University of Technology	China
Wu	Zhouyu	Hefei University of Technology	China
Wu	Zhen	North China University of Technology	China
<b>X</b>			
Xiang	Yi	Chengdu Semi-Future Technology Co. Ltd.	China
Xiao	Qiang	Zhuzhou CRRRC Times Semiconductor Co. Ltd. State Key Laboratory of Power Semiconductor and Integration Technology	China
Xie	Kevin	Wolfspeed	China
Xin	Guoqing	Huazhong University of Science and Technology	China
Xu	Dianguo	Harbin Institute of Technology	China
Xu	Sun	China Huaneng Group Clean Energy Research Institute	China

Last Name	First Name	Organisation	Country
Xu	Xiaowei	Three Gorges Intelligent Industrial Control Technology Company	China
Xu	Yi	University of Electronic Science and Technology of China	China
Xu	Yong	Gensol (Shenzhen) Tech. Innovation Center Co. Ltd.	China
<b>Y</b>			
Yamashita	Hiroshi	ROHM Co. Ltd.	Japan
Yan	Jinchun	Starpower Semiconductors Ltd.	China
Yang	Hong Qiang	University of Electronic Science and Technology of China	China
Yang	Ke	Chengdu Semi-Future Technology Co. Ltd.	China
Yang	Ming	Harbin Institute of Technology	China
Yang	Shaodong	No.5 Electronics Research Institute of the Ministry of Industry and Information Technology	China
Yang	Wuhua	Xi'an University of Technology	China
Yang	Yayong	Huazhong University of Science and Technology	China
Yang	Zhiqing	Hefei University of Technology	China
Yao	Lijun	Starpower Semiconductors Ltd.	China
Yi	Bo	University of Electronic Science and Technology of China	China
Yoneyama	Rei	Mitsubishi Electric Corporation	Japan
Yong	Fu	Starpower Semiconductors Ltd.	China
Yoshida	Kentaro	Mitsubishi Electric Corp.	Japan
Yoshida	Souichi	Fuji Electric Co. Ltd.	Japan
Young	Sungmo	Infineon Technologies Korea	South Korea
Yu	Zixiang	Hefei University of Technology	China
Yuan	Ziheng	Hefei University of Technology	China
Yue	Weixin	Harbin Institute of Technology	China
<b>Z</b>			
Zaitzu	Toshiyuki	ROHM Co. Ltd.	Japan
Zhang	Chao	Xi'an University of Technology	China
Zhang	Fulin	Wolfspeed	China
Zhang	Guofu	North China University of Technology	China
Zhang	Hao	Infineon Technologies Center of Competence (Shanghai) Co. Ltd.	China
Zhang	Junyang	China Huaneng Clean Energy Research Institute	China
Zhang	Jianning	China Resources Runan Chongqing Co. Ltd.	China
Zhang	Leon (Lizhen)	onsemi	USA
Zhang	Peilin	Avasition Electric Co. Ltd.	China
Zhang	Qiyang	Shenzhen University	China
Zhang	Ruliang	Xi'an University of Technology	China
Zhang	Tao	Macmic Science & Technology Co. Ltd.	China
Zhang	Xiaoguang	North China University of Technology	China
Zhang	Yanzi	Sichuan University	China

Last Name	First Name	Organisation	Country
Zhang	Yuancheng	Mitsubishi Electric & Electronics (Shanghai) Co. Ltd.	China
Zhao	Shuang	Hefei University of Technology	China
Zhao	Xiaodong	Harbin Institute of Technology	China
Zhao	Zhenbo	Infineon Technologies Center of Competence (Shanghai) Co. Ltd.	China
Zheng	Songlin	Starpower Semiconductors Ltd.	China
Zheng	ZeDong	Tsinghua University	China
Zhong	Ze	Shenzhen University	China
Zhou	Liwei	Infineon Technologies China Co. Ltd.	China
Zhou	Ming	Infineon Semiconductor (Shenzhen) Co. Ltd.	China
Zhou	Shuhan	Sichuan University	China
Zhou	Yimin	Huazhong University of Science and Technology	China
Zhuang	Wenrong	Dongguan Sino Nitride Semiconductor Co. Ltd.	China
Zou	Xi	Zhuzhou CRRC Times Semiconductor Co. Ltd. State Key Laboratory of Power Semiconductor and Integration Technology	China